

Ceramic Susceptor

Abstract

Ceramic susceptor whose wafer-retaining face has superior isothermal properties, and that is suited to utilization in apparatuses for manufacturing semiconductors and in liquid-crystal manufacturing apparatuses. In plate-shaped sintered ceramic body 1, resistive heating element 2 is formed. Fluctuation in pullback length L between sintered ceramic body outer-peripheral edge 1a and resistive heating element substantive-domain outer-peripheral edge 2a is within $\pm 0.8\%$, while isothermal rating of the entire surface of the wafer-retaining face is $\pm 1.0\%$ or less. Preferable is a superior isothermal rating of $\pm 0.5\%$ or less that can be achieved by bringing the fluctuation in pullback length L to within $\pm 0.5\%$.